

## **Description**

The DMG2301L uses advanced trench technology

to provide excellent  $R_{\,\text{DS}(\text{ON})},$  low gate chargeand

operation with gate voltages as low as 1.8V.

This device is suitable for use as a load switch

or in PWM applications.



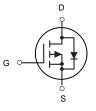
**SOT-23** 

#### **General Features**

 $V_{DS} = -20V, I_{D} = -2.3A$ 

 $R_{DS(ON)}$  < 140m  $\Omega$  @  $V_{GS}$ =-4.5V

 $R_{DS(ON)}$  < 170m  $\Omega$  @  $V_{GS}$ =-2.5V



# **Application**

PWM applications

Load switch

P-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
DMG2301L	SOT-23	HXY MOSFET	3000

## Absolute Maximum Ratings (TA=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	-20	V
Vgs	Gate-Source Voltage	±12	V
ID	Drain Current-Continuous	-2.3	А
Ідм	Drain Current-Pulsed (Note 1)	-9	А
P <sub>D</sub>	Maximum Power Dissipation	0.65	W
Тл,Твтв	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	178	°C/W



# Electrical Characteristics (T<sub>A</sub>=25 ℃ unless otherwise noted)

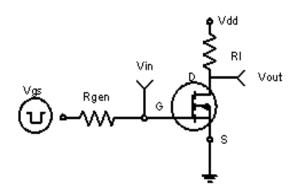
Parameter	Symbol	Symbol Condition		Тур	Max	Unit
Off Characteristics				•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA -20			-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-0.4	-0.7	-1	V
Danier Course On Otata Basistana	Б	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A		130	140	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1.8A		152	170	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-2A	4	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ - 40\/\/ -0\/	-	285	-	PF
Output Capacitance	Coss	$V_{DS}$ =-10V, $V_{GS}$ =0V, F=1.0MHz	-	58	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	Γ-1.0IVIΠ2	-	32	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	9.8	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =-10V, $R_L$ =5 $\Omega$	-	4.9	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-4.5 $V$ , $R_{GEN}$ =3 $\Omega$	-	20.5	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	nS
Total Gate Charge	Qg	\/ 40\/ L 0A	-	2.9	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-10V,I <sub>D</sub> =-2A,	-	0.45	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =-4.5V	-	0.75	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-2A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-2.0	Α

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

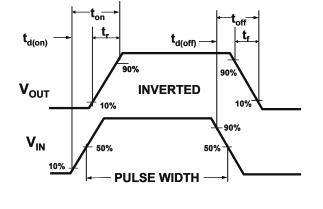
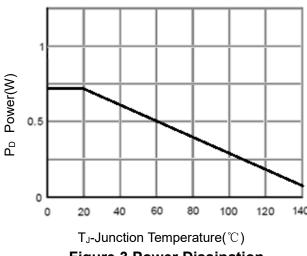
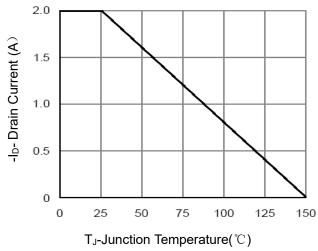


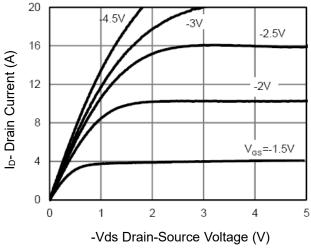
Figure 2:Switching Waveforms



**Figure 3 Power Dissipation** 



**Figure 4 Drain Current** 



**Figure 5 Output Characteristics** 

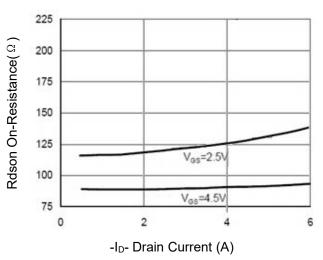
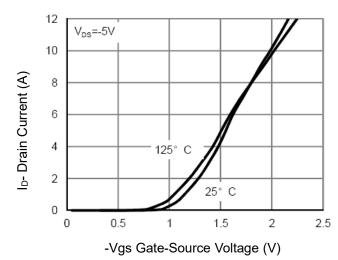


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 

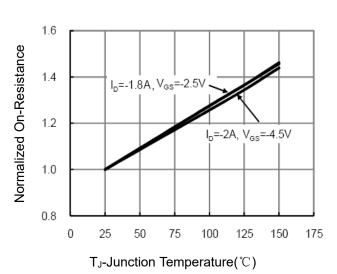
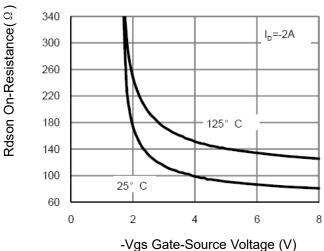


Figure 8 Drain-Source On-Resistance



-vgs Gate-Source Voltage (V

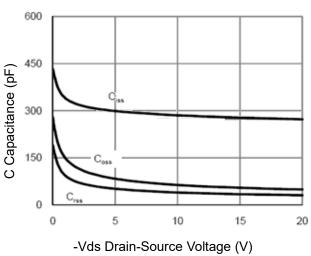


Figure 10 Capacitance vs Vds

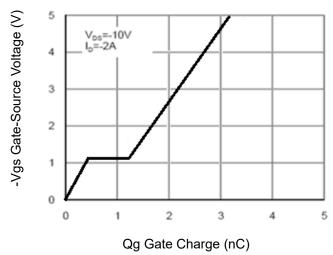


Figure 11 Gate Charge

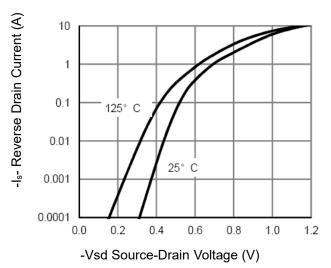


Figure 12 Source- Drain Diode Forward

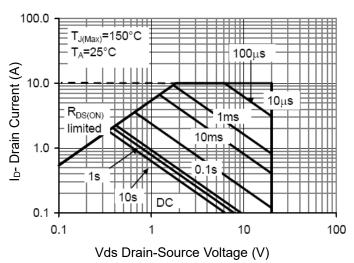
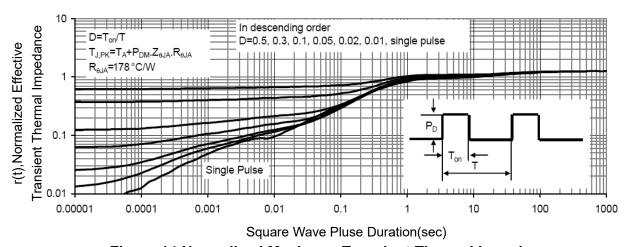
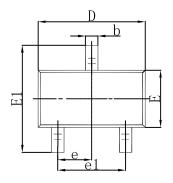


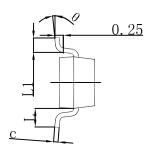
Figure 13 Safe Operation Area

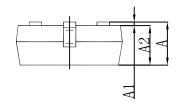


**Figure 14 Normalized Maximum Transient Thermal Impedance** 

# **SOT-23 Package Outline Dimensions**

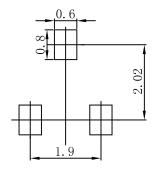






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

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